						Tilt Stage to 54	4°			
Step 1 - Platinum deposition										
Milling mode Deposition mode	Width (μm) 22	Height (μm) 3	X frequency 20,000	Y frequency 1	Milling current 300 pA	Time (s) 480	Gas ID 1 None	Gas ID 2 Platinum	Gas wait time 3	Comments Can use GIS 1 or GIS 2
						Step 2 - Carbon depos	sition			
Milling mode Deposition mode	Width (μm) 22	Height (μm) 3	X frequency 20,000	Y frequency 1	Milling current 300 pA	Time (s) 480	Gas ID 1 Carbon	Gas ID 2 None	Gas wait time 3	Comments Carbon is available only on GIS 1
					Si	tep 3a - Trapezoidal m	nilling 1			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	20	10	15	60	AI2O3	30	12 nA	0	No	Position the milling area ${\sim}0.5\mu m$ away from Pt/C deposition; Time ${\sim}19{:}54$
					C .	ton 2h Transsidal m	illing 2			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	20	10	15	60	Al2O3	30	12 nA	180	No	Use the flip option and ~5-6µm flip distance to position the milling area ~1µm away from Pt/C deposition; Time ~19:54
Milling mode)Alidah ()	llaight (um)	Denth (um)	No. of lowers	Step 4a - Rectang	gular milling - clean th	e sample walls - side 1	Anala	Treat M/D	Commente
Mill for depth	Width (μm) 20	Height (µm) 2	Depth (μm) 15	No. of layers	Al2O3	0 0	8 nA	Angle 0	No	Comments Start slightly away from the sample; Time ~ 8:52
					Step 4b - Rectana	gular milling - clean th	e sample walls - side 1			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	20	2	15	30	AI2O3	0	4 nA	0	No	Additional steps might be necessary if a clean surface is not obtained; Time \sim 14:12
					Chan An Destand	ulas milling - slaan Ab	e comunic vuelle side 2			
Milling mode	Width (um)	Height (um)	Denth (um)	No. of layers	Step 4c - Kectang Material	slone (°)	Milling current	Angle	Track WD	Comments
Mill for depth	20	2	15	30	Al2O3	0	8 nA	0	No	Use the flip option and ~3-4 µm flip distance to position the milling area
					Step 4d - Rectang	gular milling - clean th	e sample walls - side 2			
Milling mode Mill for depth	Width (μm) 20	Height (µm) 2	Depth (μm) 15	No. of layers 30	Al2O3	Slope (°) 0	Milling current 4 nA	Angle 0	No	Comments Additional steps might be necessary if a clean surface is not obtained (can check only in FIB image). Time ~ 14:12
										(can check only in the mage), time 14.12
						Tilt Stage to 0)°			
						Step 5 - J-cut Step 5a - bottom				
Milling mode	Width (µm)	Height (µm)	-	No. of Layers	-	Time (s)	Milling current	Angle	Track WD	Comments
Mill for time	20	0.75		60		200	2 n 4	190	No	Some adjustment in the position might be necessary for the cut to
Will for time	20	0.75	- Contraction of the second	00	-	200	2114	100	NO	200 - 240 s needed for this operation
						Charles The Lafe and				
Milling mode	Width (um)	Height (um)	-	No. of Lavers	-	Time (s)	e Milling current	Angle	Track WD	Comments
Mill for time	0.75	0.75	-	60	-	200	2 nA	180	No	Make sure the cut goes below the cut from step 5 a
						Chan Co. Diabh aide (m				
Milling mode	Width (um)	Height (um)	_	No. of Lavers	-	Time (s)	Milling current	Angle	Track WD	Comments
Mill for time	0.75	0.75	-	60	-	200	2 nA	180	No	Make sure the cut goes below the cut from step 5 a

Process parameters for FIB Milling Sapphire - TEM Sample Preperation

- Disable touch alarm ->check SCM on; Can be accessed from Specimen Current Monitor Menu

					Step	6a - Weld Omnipro	be to sample			
Milling mode	Width (µm)	Height (µm)	X frequency	Y frequency	Milling current	Time (s)	Gas ID 1	Gas ID 2	Gas wait time	Comments This operation must use GIS 2. It will not work with GIS 1. Check if there
Deposition mode	2.5	2.5	20,000	1	20 pA	300	None	Pt	3	is sufficient deposition
					Step 5	d - Right side (rema	ining material)			
Milling mode	Width (µm)	Height (µm)	-	No. of Layers	-	Time (s)	Milling current	Angle	Track WD	Comments
Mill for time	0.75	0.75	-	60	-	200	2 nA	180	No	Make sure the sample is properly separated
					Step	7 - TEM grid prepar	atory milling			
Milling mode	Width (µm)	Height (µm)	-	No. of Layers	-	Time (s)	Milling current	Angle	Track WD	Comments
Mill for time	14	2	-	60	-	200	2 nA	180	No	This is to create a small pocket in the TEM grid to seat the sample; Width should be ~2-3 μm larger than sample width
					6 •		and a second of			
Milling mode	Width (µm)	Height (µm)	X frequency	Y frequency	Ste Milling current	p 8 - weid TEW lam Time (s)	Gas ID 1	Gas ID 2	Gas wait time	Comments
-										This operation must use GIS 2. It will not work with GIS 1. Check if there
Deposition mode	2.5	2.5	20,000	1	20 pA	300	None	Pt	3	is sufficient deposition; reposition and repeat as necessary (2-4 times)
						Sten 9 - Detach Om	ninrohe			
Milling mode	Width (µm)	Height (µm)	-	No. of Layers		Time (s)	Milling current	Angle	Track WD	Comments
Mill for time	0.75	0.75		60	-	120	2 nA	180	No	Make sure the Omniprobe is detached from the sample; reposition and repeat if necessary
										· · · · · · · · · · · · · · · · · · ·
			- Re-	enable touch alar	m -> uncheck SCM	/l on; Can be aco	cessed from Specim	en Current Mo	nitor Menu	
						Tilt Stage to	54°			
							-			
					Ste	ep 10a - Side 1 thinn	ing (1 of 4)			
Milling mode	Width (μm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	17	1.5	10	1	AI2O3	0	2 nA	0	No	sample is too thick
					Ste	ep 10b - Side 1 thinn	ing (2 of 4)			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	16	1	10	1	Al2O3	0	300 pA	0	No	May need to be repeated if the sample is too thick
					Ste	ep 10c - Side 1 thinn	ning (3of 4)			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	15	0.6	15	1	Silicon	0	140 pA	0	No	
						Tilt Stage to 5	55 5°			
						The Stage to S	5.5			
					Ste	ep 10d - Side 1 thinn	ning (4 of 4)			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	14	0.5	15	1	Silicon	0	50 pA	0	No	
					Stag	<mark>ge Delta Rotatic</mark>	on by 180°			
					Ste	ep 11a - Side 1 thinn	ing (1 of 4)			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	17	0.7	10	1	Al2O3	0	2 nA	0	No	Start from slightly outside the sample; May need to be repeated if the sample is too thick
					Sta	on 11h - Side 1 thinn	ning (2 of 4)			
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for donth	10	0.4	15	1	Silicon	0	200 = 4	0	Ne	If not already switched, must use SE2 detector from this stage

Step 11c - Side 2 thinning (3of 4)										
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
Mill for depth	15	0.2	15	1	Silicon	0	140 pA	0	No	
Step 11d - Side 1 thinning (4 of 4)										
Milling mode	Width (µm)	Height (µm)	Depth (µm)	No. of layers	Material	Slope (°)	Milling current	Angle	Track WD	Comments
										Colorstation contails on the brinks of the how Wetch for electron
Mill for depth	14	0.3	15	1	Silicon	0	50 pA	0	No	transparency
										transparency

TEM sample preperation is complete! Tilt stage to 0°

General Comments

- All milling/deposition done at 30 kV

- Red line of the rectangles/trapezium should face the sample area

- Disable touch alarm when using Omniprobe (check SCM on), re-enable touch alarm (uncheck SCM on) after detaching Omniprobe (Specimen Current Monitor Menu)

- Each time the GIS is inserted, check the positioning on the FIB image

- Constantly check the emission current (should be 2µA)

- If the FIB shuts off after deposition, outgas the Pt (when outgassing, make sure column chamber valve is closed (Airlock menu)); Outgas option can be accessed from Gas Injection System Menu

- If no deposition is happening, Pt could be empty - notify the staff